

# 2.4MHz 3.5A Step-Down Converter with I<sup>2</sup>C Interface

### **General Description**

The RT5733 is a step-down switching voltage regulator that delivers a digitally programmable output from an input voltage supply of 2.5V to 5.5V. The output voltage is programmed through an I<sup>2</sup>C interface and is capable of operating up to 3.4MHz.

Using a proprietary architecture with synchronous rectification, the RT5733 is capable of delivering continuous 3.5A, maintaining that efficiency at load currents as low as 10mA. The regulator operates at a nominal fixed frequency of 2.4MHz, which reduces the external component counts. Additional output capacitance can be added to improve regulation during load transients without affecting stability.

At moderate and light loads, Pulse Frequency Modulation (PFM) is used to operate in power-save mode with a typical quiescent current of  $45\mu A$  at room temperature. Even with such a low quiescent current, the part exhibits excellent transient response during large load swings. At higher loads, the system automatically switches to fixed frequency control, operating at 2.4MHz. In shutdown mode, the supply current is typically  $0.1\mu A$ , and is excellent in reducing power consumption. The PFM mode can be disabled if the fixed frequency is desired. The RT5733 is available in both WQFN-20L 3.5x3.5 and WL-CSP-15B 1.31x2.02 (BSC) package.

### **Features**

- Programmable Output Voltage Range
   0.27V to 1.4V, 6.25mV/bit
- Programmable Slew Rate for Voltage Transitions
- Steady 2.4MHz Switching Frequency
- Fast Load Transient
- Continuous Output Current Capability: 3.5A
- 2.5V to 5.5V Input Voltage Range
- Digitally Programmable Output Voltage
- I<sup>2</sup>C-Compatible Interface Up to 3.4Mbps
- PFM Mode for High Efficiency at Light Load
- Quiescent Current in PFM Mode: 45μA (Typical)
- Input Undervoltage Lockout (UVLO)
- Thermal Shutdown and Overload Protection
- Power Good Indicator

### **Applications**

- · Application, Graphic, and DSP Processors
- ARM<sup>TM</sup>, Tegra<sup>TM</sup>, OMAP<sup>TM</sup>, NovaThor<sup>TM</sup>, ARMADA<sup>TM</sup>, Krait<sup>TM</sup>, etc.
- Hard Disk Drives, LPDDR3, LPDDR4, LPDDR5
- Tablets, Netbooks, Ultra-Mobile PCs
- Smart Phones
- Gaming Devices

## **Ordering Information**

Dout No.	Power-Up	Defaults	EN Delay	Slave	Dookses Type	Lead Plating	
Part No.	VSEL0	VSEL1	Time	Address	Package Type	System	
RT5733AGQW	0.5V	0.9V	0ms	0x50	WQFN-20L 3.5x3.5	G: Green (Halogen Free and Pb Free)	
RT5733AWSC	0.5V	0.9V	0ms	0x50	WL-CSP-15B 1.31x 2.02		

#### Note:

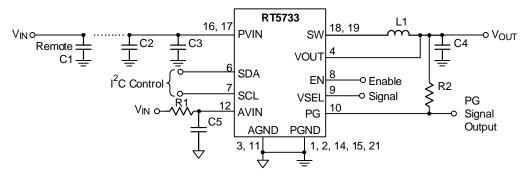
Richtek products are:

- ▶ RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- ▶ Suitable for use in SnPb or Pb-free soldering processes.

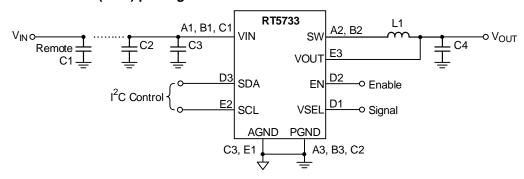


## **Simplified Application Circuit**

### For WQFN-20L 3.5x3.5 package

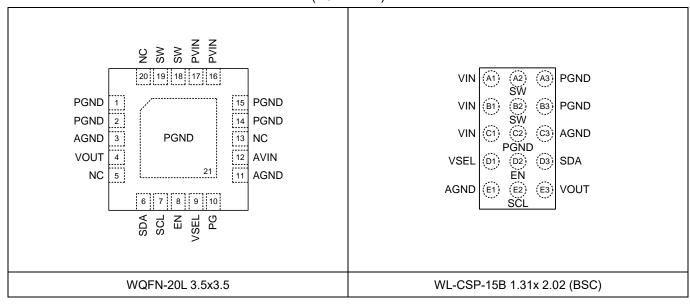


### For WL-CSP-15B 1.31x2.02 (BSC) package



## **Pin Configuration**

(TOP VIEW)





## **Marking Information**

RT5733AWSC **BGW** 

**BG**: Product Code W : Date Code

RT5733AGQW

2G=YM DNN 2G=: Product Code YMDNN: Date Code

# **Functional Pin Description**

Pin	No.						
WQFN-20L 3.5x3.5	WL-CSP-15B 1.31x 2.02 (BSC)	Pin Name	Pin Function				
1, 2, 14, 15, 21 (Exposed Pad)	A3, B3, C2	PGND	Power ground. The low-side MOSFET is referenced to this pin. The CIN and COUT should be returned with a minimal path to these pins.  The exposed pad is internally connected with PGND and must be soldered to a large PGND plane. Connect this PGND plane to other layers with thermal vias to help dissipate heat from the device.				
3, 11	C3, E1	AGND	Analog ground. All signals are referenced to this pin. Avoid routing high dV/dt AC currents through this pin.				
4	E3	VOUT	Output feedback sense pin. Output voltage sense through this pin. Connect to output capacitor.				
5, 13, 20		NC	No internal connection.				
6	D3	SDA	I <sup>2</sup> C serial data.				
7	E2	SCL	I <sup>2</sup> C serial clock.				
8	D2	EN	Enable control input. A logic-high enables the converter. A logic-low forces the device into shutdown mode, and all registers will reset to default values.				
9	D1	VSEL	Output voltage and operation mode selection pin. When this pin is low, VOUT is set by the VSEL0 register. When this pin is high, VOUT is set by the VSEL1 register. Except the output voltage setting, operation mode can also be configured and selected by the VSEL pin; for example, when 0x02 Bit1 & Bit0 are equal to 0, then VSEL0 = Auto PFM/PWM mode, and VSEL1 = Auto PFM/PWM mode. Please refer to the I <sup>2</sup> C register map for more details.				
10		PG	Power good indicator. The output of this pin is an opendrain with external pull-up resistor. After soft-startup, PG is pulled up when the FB voltage is within 90% (typ.). The PG status is low while EN is disabled. Note that when VIN is lower than 2.32V (typ.), the PG pin will keep low to indicate the power is not ready.				

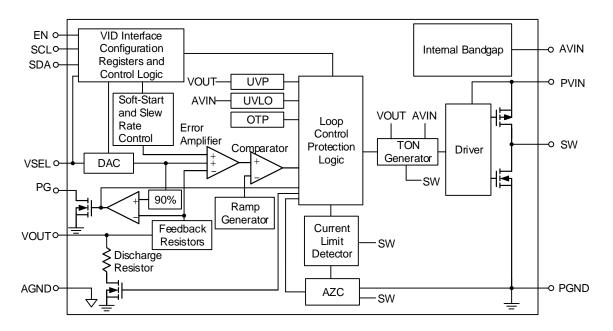


Pin	No.						
WQFN-20L 3.5x3.5	WL-CSP-15B 1.31x 2.02 (BSC)	Pin Name	Pin Function				
12		AVIN	Power supply input for internal circuit. Decouple with a $2.2\mu F$ , X5R ceramic capacitor from AVIN to AGND for normal operation.				
16, 17	A1, B1, C1	PVIN	Power input voltage. Connect to the input power source. Connect to CIN with minimal path.				
18, 19	A2, B2	SW	Switching node. Connect to the inductor.				

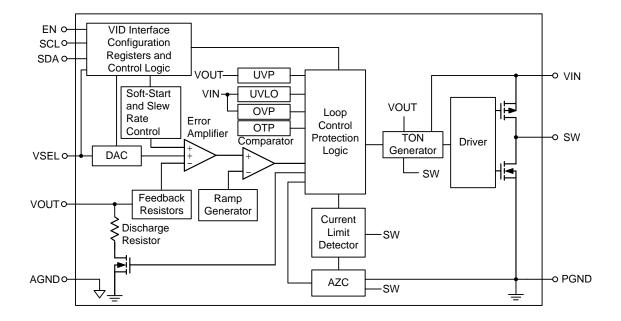


## **Functional Block Diagram**

### For WQFN-20L 3.5x3.5 package



### For WL-CSP-15B 1.31x 2.02 (BSC) package



DS5733-00



### **Operation**

The RT5733 is a low voltage synchronous step-down converter that can support input voltage ranging from 2.5V to 5.5V, and the output current can be up to 3.5A. The RT5733 uses ACOT® mode control. To achieve good stability with low-ESR ceramic capacitors, the ACOT® uses a virtual inductor current ramp generated inside the IC. This internal ramp signal replaces the ESR ramp normally provided by the output capacitor's ESR. The ramp signal and other internal compensations are optimized for low-ESR ceramic output capacitors.

In steady-state operation, the feedback voltage, with the virtual inductor current ramp added, is compared to the reference voltage. When the combined signal is less than the reference, the on-time one-shot is triggered, as long as the minimum off-time one-shot is cleared and measured inductor current (through synchronous rectifier) is below the current limit. The ontime one-shot turns on the high-side switch and the inductor current ramps up linearly. After the on-time, the high-side switch is turned off, the synchronous rectifier is turned on, and the inductor current ramps down linearly. At the same time, the minimum off-time oneshot is triggered to prevent another immediate on-time during the noisy switching times and allows the feedback voltage and current sense signals to settle. The minimum off-time is kept short so that rapidlyrepeated on-times can raise the inductor current guickly when needed.

#### **PWM Frequency and Adaptive On-Time Control**

The on-time can be roughly estimated by the equation:

$$T_{ON} = \frac{V_{OUT}}{V_{IN}} \times \frac{1}{f_{SW}}$$

where fsw is nominal 2.4MHz.

### **Undervoltage Protection (UVLO)**

The UVLO continuously monitors the voltage of VIN to make sure the device works properly. When the VCC is high enough to reach the high threshold voltage of UVLO, the step-down converter softly starts or prebiases to its regulated output voltage. When the VIN decreases to its low threshold (350mV hysteresis), the device will shut down.

#### Power GOOD (Register, 0x05 bit7)

When the output voltage is higher than PGOOD rising threshold (90% of its setting voltage), the PGOOD flag is high.

#### Power Good Indication Pin (only parts with PG pin)

The RT5733 features an open-drain power-good output (PG) to monitor the output voltage status. The output delay of comparator prevents false flag operation for short excursions in the output voltage, such as during line and load transients. Pull up PG with a resistor to Vout or an external voltage below 5.5V. When VIN voltage rises above VUVLO, the power-good function is activated. After soft-start is finished, the PG pin is controlled by a comparator connected to the feedback signal Vout. If Vout rises above a power-good high threshold (VTH\_PGLH) (typically 90% of the reference voltage), the PG pin will be in high impedance and VPG will be held high. Moreover, when VIN is above UVLO and device is powered on through the EN pin, the PG pin will assert high within 300µs as soon as the VEN is above logic-high threshold; in other words, the PG delay time is around 300 µs from EN asserts to logic-high.

When Vour falls below the power-good low threshold (VTH\_PGHL) (typically 80% of the reference voltage), the PG pin will be pulled low after a certain delay (3µs, typically). Once being started-up, if any internal protection is triggered, PG will be pulled low to GND. The internal open-drain pull-down device (11 $\Omega$ , typically) will pull the PG pin low. Note that when Vin is lower than 2.32V, the PG pin will keep low to indicate the power is not ready.

## **Output Undervoltage Protection (UVP) and Overcurrent Protection (OCP)**

When the output voltage of the RT5733 is lower than 59% of the reference voltage after soft-start, the UVP is triggered.

The RT5733 senses the current signal when high-side and low-side MOSFETs turn on. As a result, the OCP is cycle-by-cycle limit. If the OCP occurs, the converter holds off the next pulse and turns on low-side switch



until inductor drops below the valley current limit, and then turns on high-side again to maintain output voltage and supports loading current to output before triggering UVP.

If the OCP condition keeps and the load current is larger than the current that the converter can provide, the output voltage will decrease and drop below UVP threshold, and the converter will keep switching for 16 consecutive cycles before it enters hiccup operation. The converter latches off 1.7ms when the output voltage is still lower than UVP threshold, and the soft-start sequence begins again after latching off time.

Note that, there is sensing propagation delay time before triggering OCP; hence, the OCP may take a few cycles to occur when the inductor current is near OCP threshold. If the output voltage drops slowly before entering hiccup operation, the converter will extend the high-side switch on-time and turns on low-side switch for only minimum off-time to provide large load current and catch up with the output voltage before detecting peak current limit OCP.

#### Soft-Start

An internal current source charges an internal capacitor to build the soft-start ramp voltage. The typical soft-start time can be programmed by  $I^2C$ .

### **Over-Temperature Protection (OTP)**

The RT5733 has over-temperature protection. When the device triggers the OTP, the device shuts down immediately, and will soft-start again when the junction temperature is below the recovery threshold.



### **Absolute Maximum Ratings** (Note 1)

Supply Input Voltage, PVIN, AVIN	0.3V to 7V
SW Pin Switch Voltage, SW	−1V to 7.3V
<50ns	−5V to 8.5V
Other I/O Pin Voltages	-0.3V to 7V
• Lead Temperature (Soldering, 10 sec.)	260°C
• Junction Temperature	150°C
Storage Temperature Range	–65°C to 150°C

## **ESD Ratings**

• ESD Susceptibility (Note 2) HBM (Human Body Model) ----- 2kV

## **Recommended Operating Conditions** (Note 3)

•	Supply Input Voltage, PVIN	2.5V to 5.5V
•	Supply Input Voltage, AVIN	2.5V to 5.5V
•	Ambient Temperature Range	-40°C to 85°C

## Thermal Information (Note 4 and Note 5)

	Thermal Parameter	WQFN-20L 3.5x3.5	WL-CSP-15B 1.31x2.02	Unit
θЈА	Junction-to-ambient thermal resistance (JEDEC standard)	28.6	42	°C/W
$\theta$ JC(Top)	Junction-to-case (top) thermal resistance	55.6	0.2	°C/W
$\theta$ JC(Bottom)	Junction-to-case (bottom) thermal resistance	2.3	9.5	°C/W
θJA(EVB)	Junction-to-ambient thermal resistance (specific EVB)	43.2	49.9	°C/W
ΨJC(Top)	Junction-to-top characterization parameter	5.4	1.1	°C/W
ΨЈВ	Junction-to-board characterization parameter	21.8	27.7	°C/W



### **Electrical Characteristics**

 $(V_{IN} = V_{AVIN} = V_{PVIN} = 3.6V, T_A = 25$ °C, unless otherwise specified)

Pa	rameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Operating Q PWM	uiescent Current	IQ_PWM	ILOAD = 0, mode Bit = 1 (Forced PWM) (Note 6)		15		mA
Operating Q PFM	uiescent Current	IQ_PFM	ILOAD = 0A		45		μА
Operating Le	ow Power Mode Current PFM	IQ_PFM_LPM	ILOAD = 0A and Enable LPM		36		μА
H/W Shutdo Current	wn Supply	Ishdn_h/w	EN = GND		0.1	3	μА
S/W Shutdo Current	wn Supply	Ishdn_s/w	EN = VIN, BUCK_ENx = 0, 2.5V ≤ VIN ≤ 5.5V		2	12	μА
Undervoltag Threshold	e Lockout	Vuvlo	VIN rising		2.32	2.45	V
Undervoltag Hysteresis	e Lockout	ΔVυνιο			350		mV
RDS(ON) of F	P-MOSFET	RDS(ON)_P	VIN = 5V		30		mΩ
RDS(ON) of N	N-MOSFET	RDS(ON)_L	VIN = 5V		17		mΩ
Input	Logic-High	ViH	2.5V ≤ VIN ≤ 5.5V	1.1			V
Voltage	Logic-Low	VIL	$2.5V \le V_{IN} \le 5.5V$			0.4	V
EN Input Bia	as Current	len	EN input tied to GND or VIN		0.01	1	μΑ
			$ \begin{array}{l} 2.8 \text{V} \leq \text{V}_{\text{IN}} \leq 4.8 \text{V}, \text{ V}_{\text{OUT}} \text{ from} \\ \text{Minimum to Maximum,} \\ \text{I}_{\text{OUT}(\text{DC})} = 0 \text{ to } 3\text{A}, \text{ V}_{\text{OUT}} > 0.6 \text{V}, \\ \text{Auto PFM/PWM} \qquad (\text{Note 6}) \\ \end{array} $			3	%
Vous DC As			$2.8V \le VIN \le 4.8V$ , VOUT from Minimum to Maximum, IOUT(DC) = 0 to 3A, VOUT $\le 0.6V$ , Auto PFM/PWM (Note 6)	-18		18	mV
VOUT DC A	ecuracy			-2		2	%
			$ \begin{array}{l} 2.8 \text{V} \leq \text{V}_{\text{IN}} \leq 4.8 \text{V},  \text{V}_{\text{OUT}}  \text{from} \\ \text{Minimum to Maximum,} \\ \text{IOUT(DC)} = 0  \text{to } 3 \text{A},  \text{V}_{\text{OUT}} \leq 0.6 \text{V}, \\ \text{Forced PWM} \qquad (\text{Note 6}) \\ \end{array} $	-12		12	mV
Load Regula	ation	$\Delta V$ LOAD	IOUT(DC) = 1 to 3A (Note 6)		0.1		%/A
Line Regula	tion	ΔVLINE	$2.5V \le V_{IN} \le 5.5V$ , $I_{OUT(DC)} = 1.5A$ (Note 6)		0.2		%/V



Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
		ILOAD step 0.01A to 1.5A, tR = tF = 500ns, VouT = 1.125V (Note 6)		±45			
Transient Load Response	ACLOAD	ILOAD step 0.1A to 1.8A, tR = tF = 1 $\mu$ s, VIN = 3.8V, VOUT = 0.9V (Note 6)		±56		mV	
		ILOAD step 0.01A to 0.8A, tR = tF = 1 $\mu$ s, L = 0.33 $\mu$ H, COUT = 22 $\mu$ F x 2 (Note 6)		45			
Line Transient	VLINE	$V_{IN} = 3V$ to 3.6V, $t_R = t_F = 10 \mu s$ , $l_{OUT} = 100 mA$ , Forced PWM mode (Note 6)		±40		mV	
P-MOSFET Peak Current Limit	ILIM_P		5	5.5	6	А	
Valley Current Limit			3.5	4	4.5	Α	
Thermal Shutdown	TsD			150		°C	
Thermal Shutdown Hysteresis	ΔTSD			15		°C	
Input OVP Shutdown	VSDHD_OVPrth	Rising threshold		6.15		V	
Input OVP Shutdown	VSDHD_OVPfth	Falling threshold	5.5	5.73		V	
Switching Frequency	fsw	Vout = Default RT5733AGQW: 0.5V RT5733AWSC: 0.5V	2100	2400	2700	kHz	
Minimum Off-Time	toff_MIN			170		ns	
DAC Resolution		(Note 6)		8		bits	
DAC Differential Nonlinearity		(Note 6)			0.5	LSB	
I <sup>2</sup> C Interface (Note 6)							
CDA CCL Input Voltage	High Level		1.2			W	
SDA, SCL Input Voltage	Low Level				0.4	V	
		Fast mode			400	kHz	
SCL Clock Rate	fscL	Fast plus mode			1	MHz	
		High speed mode, load 100pF max			3.4	MHz	
Hold Time (Repeated) Start		Fast mode	0.6				
Condition. After this Period, the First Clock Pulse is	thd;sta	Fast plus mode	0.26			μS	
Generated		High speed mode	0.16				
		Fast mode	1.3				
Low Period of the SCL Clock	tLOW	Fast plus mode	0.5			μS	
		High speed mode	0.16				
		Fast mode	0.6				
High Period of the SCL Clock	tніgн	Fast plus mode	0.26			μS	
		High speed mode	0.06				



Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit				
		Fast mode	0.6							
Set-Up Time for a Repeated START Condition	tsu;sta	Fast plus mode	0.26			μS				
OTATO Condition		High speed mode	0.01							
		Fast mode	0							
Data Hold Time	tHD;DAT	Fast plus mode	0			μS				
		High speed mode	0							
		Fast mode	100							
Data Set-Up Time	tsu;dat	Fast plus mode	50			ns				
		High speed mode	10							
		Fast mode	0.6							
Set-Up Time for STOP Condition	tsu;sto	Fast plus mode	0.26			μS				
		High speed mode	0.16							
Bus Free Time between a	4	Fast mode	1.3			_				
STOP and START Condition	tBUF	Fast plus mode	0.5			μS				
	Fast plus mode 0  Fast mode 2	20		300	ns					
		Fast plus mode			120	ns				
Rising Time of both SDA and SCL Signals	t <sub>R</sub>	High speed mode (SDA) load 100pF max	10		80	ns				
		High speed mode (SCL) load 100pF max	10		40	ns				
		Fast mode	20 x (V <sub>DD</sub> /5.5V)		300	ns				
Falling Time of both SDA	4-	Fast plus mode	20 x (V <sub>DD</sub> /5.5V)		120	ns				
and SCL Signals	tF	High speed mode (SDA) load 100pF max	10		80	ns				
		High speed mode (SCL) load 100pF max	10	1	40	ns				
SDA Output Low Sink Current	loL	SDA voltage = 0.4V	2			mA				

- **Note 1.** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.
- Note 2. Devices are ESD sensitive. Handling precautions are recommended.
- **Note 3.** The device is not guaranteed to function outside its operating conditions.
- Note 4. For more information about thermal parameter, see the Application and Definition of Thermal Resistances report, AN061.
- Note 5.  $\theta_{JA(EVB)}$ ,  $\Psi_{JC(Top)}$  and  $\Psi_{JB}$  are measured on a high effective-thermal-conductivity four-layer test board which is in size of 70mm x 50mm; furthermore, all layers with 1 oz. Cu. Thermal resistance/parameter values may vary depending on the PCB material, layout, and test environmental conditions.
- Note 6. Guaranteed by design.



## **Typical Application Circuit**

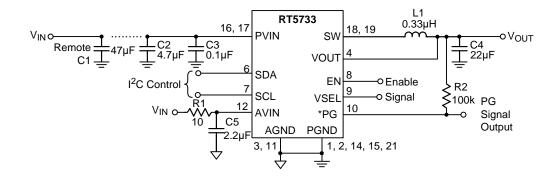


Figure 1. RT5733 WQFN-20L 3.5x3.5 Package Typical Application Circuit

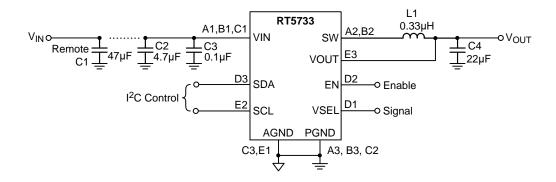


Figure 2. RT5733 WL-CSP-15B 1.31x 2.02 (BSC) Package Typical Application Circuit

Component Vendor P/N Description 330nH, case size DFE201610E-R33M=P2 (Murata) L1 470nH, case size DFE201610E-R47M=P2 (Murata)  $4.7\mu F$ , 10V, X5R, 0402C2 GRM155R61A475MEAA (Murata) C3<sup>(1)</sup> 100nF, 6.3V, X5R, 0201 GRM033R60J104KE19D (Murata) GRM188R60J226MEA0D (Murata) C4 22μF, 6.3V, X5R, 0603 C1608X5R0J226M080AC (TDK)

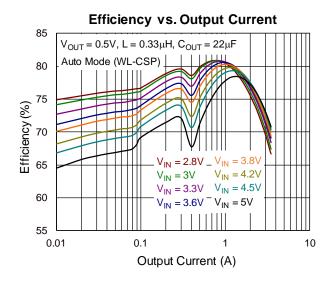
Table 1. Recommended External Components for 3.5A Maximum Load Current

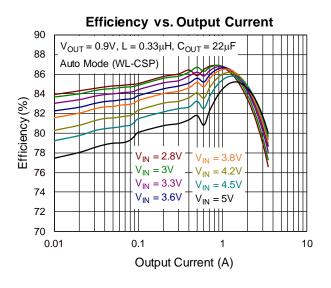
#### Note:

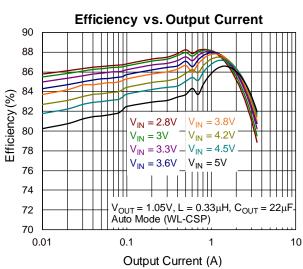
- (1) The decouple capacitor C3 is recommended to reduce any high frequency component on VIN bus. C3 is optional and used to filter any high frequency component on VIN bus.
- (2) All the input and output capacitors are the suggested values, referring to the effective capacitances, subject to any de-rating effect, like a DC bias.

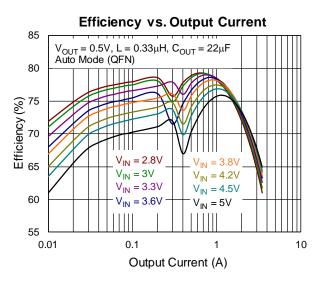


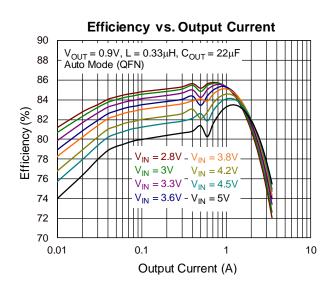
### **Typical Operating Characteristics**

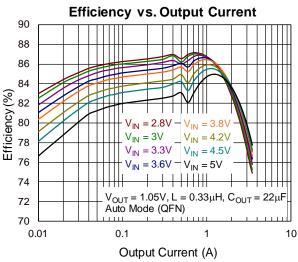












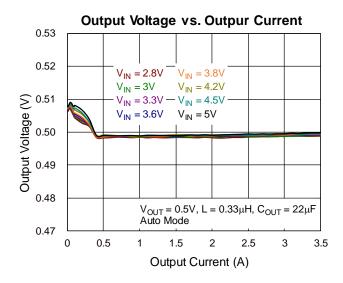
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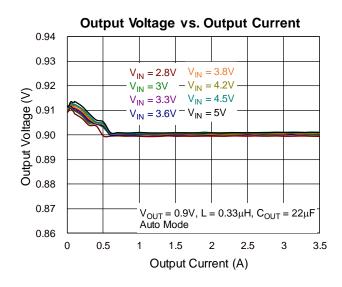
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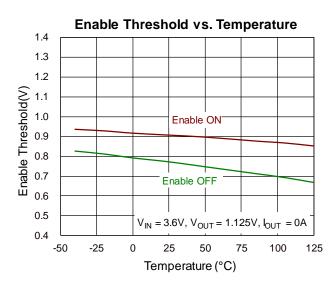
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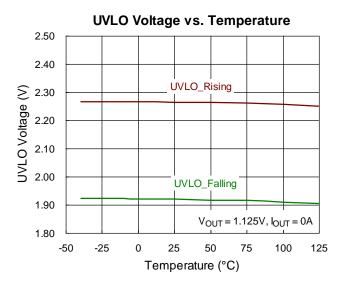
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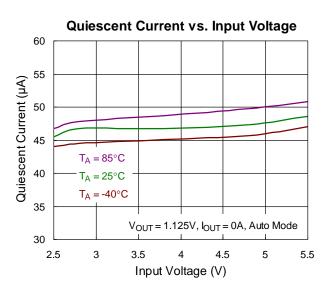


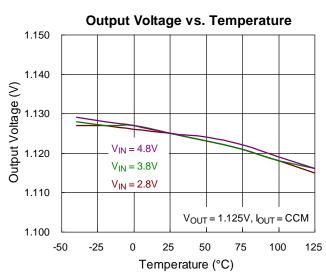




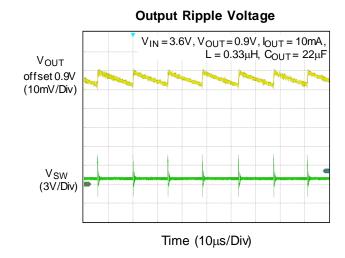


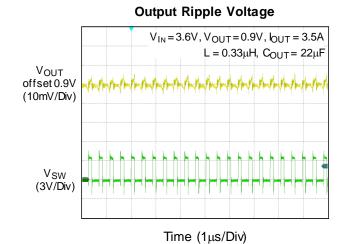


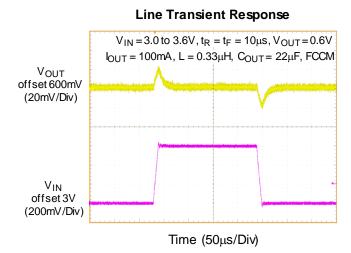


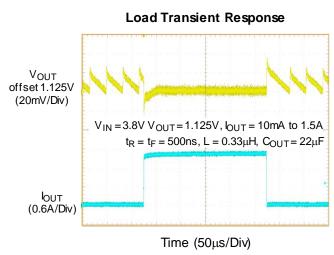


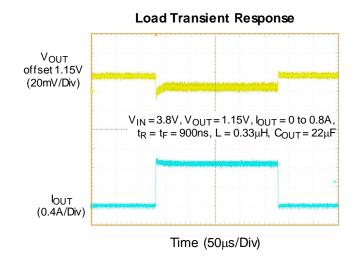


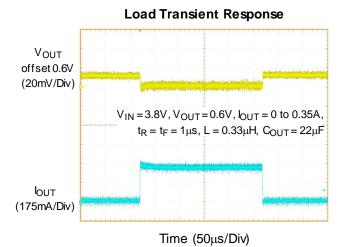








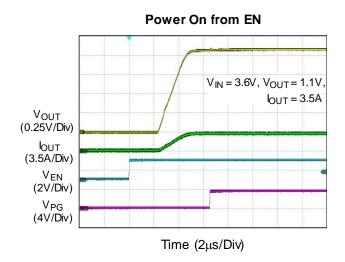


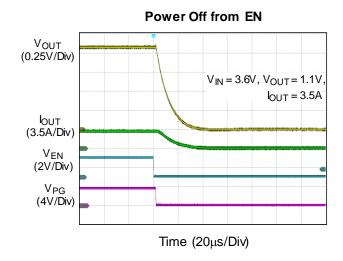


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### **Application Information**

Richtek's component specification does not include the following information in the Application Information section. Thereby no warranty is given regarding its validity and accuracy. Customers should take responsibility to verify their own designs and to ensure the functional suitability of their components and systems.

The basic RT5733 application circuit is shown in Typical Application Circuit. External component selection is determined by the maximum load current and begins with the selection of the inductor value, operating frequency, and followed by CIN and COUT.

#### **Inductor Selection**

The inductor value and operating frequency determine the ripple current according to a specific input and output voltage. The ripple current,  $\Delta I_L$ , increases with higher  $V_{IN}$  and decreases with higher inductance, as shown in the equation below:

$$\Delta I_{L} = \left[ \frac{V_{OUT}}{f \times L} \right] \times \left[ 1 - \frac{V_{OUT}}{V_{IN}} \right]$$

where f is the operating frequency and L is the inductance. Lower ripple current reduces not only ESR losses in the output capacitors, but also the output voltage ripple. Higher operating frequency combined with smaller ripple current is necessary to achieve high efficiency. Thus, a large inductor is required to attain this goal.

The largest ripple current occurs at the highest VIN. A reasonable starting point for selecting the ripple current is  $\Delta IL = 0.3$  x IMAX to 0.4 x IMAX. To guarantee that the ripple current stays below a specified maximum, the inductor value should be chosen according to the following equation:

$$L = \left[\frac{V_{OUT}}{f \times \Delta I_{L(MAX)}}\right] \times \left[1 - \frac{V_{OUT}}{V_{IN(MAX)}}\right]$$

#### **Input and Output Capacitor Selection**

An input capacitor, CIN, is needed to filter out the trapezoidal current at the source of the high-side MOSFET.

To prevent large ripple current, a low ESR input capacitor sized for the maximum RMS current should be used. The RMS current is given by:

$$I_{RMS} = I_{OUT(MAX)} \times \frac{V_{OUT}}{V_{IN}} \times \sqrt{\frac{V_{IN}}{V_{OUT}}} - 1$$

This formula has a maximum at  $V_{IN} = 2V_{OUT}$ , where  $I_{RMS} = I_{OUT}(MAX)/2$ .

This simple worst-case condition is commonly used for design.

Choose a capacitor rated at a higher temperature than required.

Several capacitors may also be paralleled to meet the size or height requirements of the design. Ceramic capacitors have high ripple current, high voltage rating and low ESR, which makes them ideal for switching regulator applications.

However, they can also have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can lead to significant ringing. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input, VIN. At best, this ringing can couple to the output and be mistaken as loop instability. At worst, a sudden inrush of current through the long wires can potentially cause a voltage spike at VIN large enough to damage the part. Thus, care must be taken to select a suitable input capacitor.

The selection of Cout is determined by the required ESR to minimize output voltage ripple. Moreover, the amount of bulk capacitance is also a key for Cout selection to ensure that the control loop is stable. Loop stability can be checked by viewing the load transient response.

The output voltage ripple,  $\Delta V_{OUT}$ , is determined by:

$$\Delta V_{OUT} \le \Delta I_L \Bigg[ \text{ESR} + \frac{1}{8 \times f_{SW} \times C_{OUT}} \Bigg]$$

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#### I<sup>2</sup>C Interface Function

The RT5733 uses the I<sup>2</sup>C interface to select VOUT voltage level, Dynamic Voltage Scaling (DVS) slew rate, Auto PFM/PSM or FCCM mode, and so on. The register of each function can be found from the following register map and it also explains how to use these functions.

#### **VOUT Selection**

The RT5733 all series products have programmable output voltage range from 0.27V to 1.4V with 6.25mV/bit resolution. Note that, the output voltage can be set by the NSELx register bit and the output voltage are given by the following equation and examples:

 $VOUT = 0.27V + NSELx \times 6.25mV$ 

For example:

if NSELx = 0111100 (60 decimal), then

 $VOUT = 0.27 + 60 \times 6.25 \text{mV}$ 

= 0.27 + 0.375 = 0.645V.

The RT5733 also has external VSEL pin to select NSEL1(0x01) or NSEL0(0x00). Pull VSEL to high is for VSEL1 and pull VSEL to low is for VSEL0. Upon POR, VSEL0 and VSEL1 are reset to their default voltages.

#### **Enable and Soft-Start**

When the EN pin is LOW, the IC is shut down, all internal circuits are off, and the part draws very little current. In this state,  $I^2C$  cannot be written or read until input voltage is above the UVLO. The registers will reset when the EN pin is LOW or during a Power-On Reset (POR).

Once the EN pin is high, VOUT will ramp up at the chosen soft-start slew rate programmed in the CONTROL2 register SS\_SR bit.

Raising EN while the EN\_VSELx bit is HIGH activates the part and begins the soft-start cycle.

### Discharge Function

In the CONTROL1 register, set the DISCHG bit to 1 can make Vout discharge by internal resistor when the converter shuts down. If the DISCHG bit is set to 0, Vout will decrease depending on the loading. When the EN pin is set to low, the RT5733 will default turn on internal  $11\Omega$  discharge resistor.

#### **Slew Rate Setting**

The RT5733 can control slew rate as Vout changing between two voltage levels for both up and down.

In the CONTROL1 register, DVS\_UP bits can control up-speed. In the CONTROL2 register, DVS\_DN can control down-speed. The default slew rate of DVS\_UP is  $12mV/\mu s$  and the slew rate of DVS\_DN is  $3mV/\mu s$ .

The details of slew rate setting can be found in the register function description table.

### **Operation Mode Selection**

In the CONTROL1 register, MODE\_VSEL0 and MODE\_VSEL1 can decide whether the converter is always at FCCM mode or enters power saving mode at light load conditions.

In auto PFM mode, the auto zero current detector circuit senses the SW waveform to adjust the zero current threshold voltage. When the current of low-side MOSFET decreases to the zero current threshold, the low-side MOSFET turns off to prevent negative inductor current. In this way, the zero current threshold can be adjusted for different conditions to get better efficiency.

The default operation mode of MODE\_VSEL0 is auto PFM mode and MODE\_VSEL1 can be selected by factory setting.

When output voltage is changing from high to low, the RT5733 will make transition operation at PWM mode and output voltage will decrease quickly.

#### **Low Power Mode Operation**

RT5733 features auto PFM/PWM mode to achieve power-saving operation. It generates a single switching pulse to ramp up the inductor current and recharges the output capacitor, followed by a skip pulse or a sleep period to cut down current demand from input source to obtain high efficient at light load conditions. The load current is supported by the output capacitor during this sleep period depending on the load current and the inductor peak current.

To minimize the battery energy consumption, the system requests further quiescent current reduction operation such as shipping mode or suspend operation, etc. RT5733 features low power mode (LPM) operation, where several of the internal protection circuits (input

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DS5733-00



OVP, UVP) are shutdown to achieve lowest  $36\mu A$  operating quiescent current for ultra-light load condition. LPM operation can be enabled by setting LPM control register (0x0A bit1) to 1 in the CONTROL5 register.

### I<sup>2</sup>C Time Out Function

The RT5733 has built-in  $I^2C$  time out function to make RT5733 resume listening state during communication bus error situation.

When RT5733 detects whether the SCL pin or SDA pin is pulled down for more than 30ms, RT5733 will reset its  $I^2C$  interface. The  $I^2C$  time out function can be enabled or disabled by control register (0x0A bit0). For more detail setting value, please refer to  $I^2C$  register table.

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#### I<sup>2</sup>C Interface

The all series of RT5733 are able to support fast mode  $I^2C$  interface (bit rate 400kb/s), and different parts have their own slave address. For example, the default  $I^2C$  slave address of the RT5733AGQW is 7'b1010000. The write or read bit stream (N  $\geq$  1) is shown below:

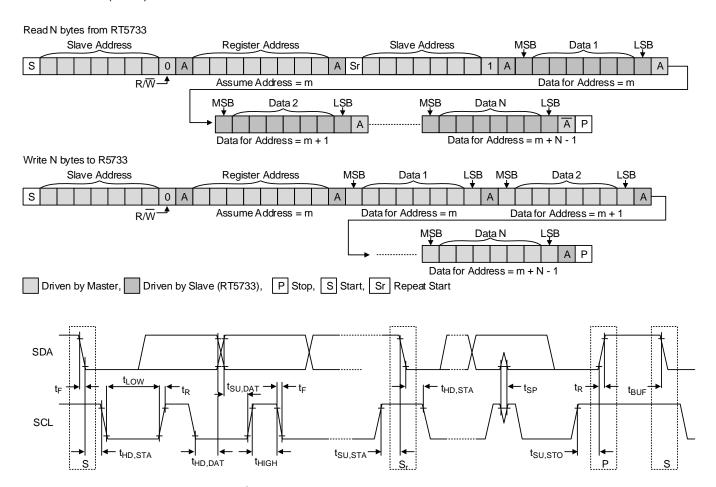


Figure 3. I<sup>2</sup>C Read and Write Stream and Timing Diagram

The RT5733 also supports High-speed mode (bit rate up to 3.4Mb/s) with access code 08H. Figure 4 and Figure 5 show detailed transfer format. Hs-mode can only commence after the following conditions (all of which are in F/S-mode):

- START condition (S)
- 8-bit master code (00001xxx)
- Not-acknowledge bit (A)

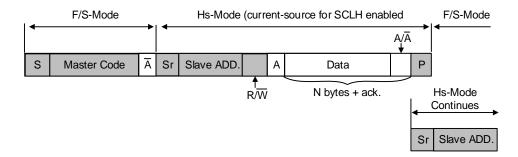


Figure 4. Data Transfer Format in HS-Mode

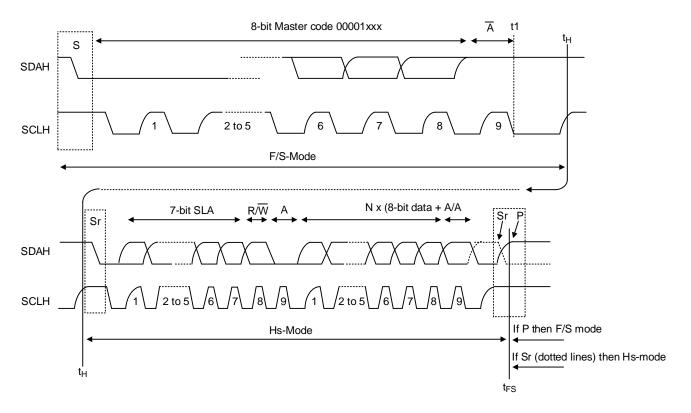


Figure 5. A Complete HS-Mode Transfer



#### **Thermal Considerations**

The junction temperature should never exceed the absolute maximum junction temperature T<sub>J</sub>(MAX), listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula:

 $PD(MAX) = (TJ(MAX) - TA)/\theta JA$ 

where T<sub>J</sub>(MAX) is the maximum junction temperature, T<sub>A</sub> is the ambient temperature, and  $\theta_{JA}$  is the junction-toambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance,  $\theta_{JA(EVB)}$ , is highly package dependent. For a WQFN-20L 3.5x3.5 package, the thermal resistance,  $\theta_{JA(EVB)}$ , is 43.2°C/W on a high effective-thermal-conductivity four-layer test board. For a WL-CSP-15B 1.31x2.02 (BSC) package, the thermal resistance,  $\theta_{JA(EVB)}$ , is 49.9°C/W on a high effectivethermal-conductivity four-layer test board. maximum power dissipation for both package at T<sub>A</sub> = 25°C can be calculated as below:

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ}C)/(43.2^{\circ}C/W) = 2.3W$  for a WQFN-20L 3.5x3.5 package.

 $PD(MAX) = (125^{\circ}C - 25^{\circ}C)/(49.9^{\circ}C/W) = 2W \text{ for a}$ WL-CSP-15B 1.31x2.02 (BSC) package.

The maximum power dissipation depends on the operating ambient temperature for the fixed T<sub>J</sub>(MAX) and the thermal resistance,  $\theta$ JA(EVB). The derating curves in Figure 6 allows the designer to see the effect of rising ambient temperature on the maximum dissipation.

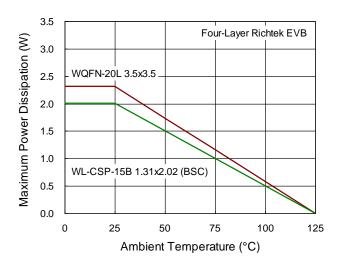


Figure 6. Derating Curve of Maximum Power Dissipation

#### **Layout Considerations**

For best performance of the RT5733, the following layout guidelines must be strictly followed.

- ▶ Input capacitor must be placed as close as possible to the IC to minimize the power loop area. A typical  $0.1 \mu F$  decouple capacitor is recommended to reduce power loop area and any high frequency component on PVIN.
- ▶ SW node is with high frequency voltage swing and should be kept at small area. Keep analog components away from the SW node to prevent stray capacitive noise pickup.
- ▶ Keep every power trace connected to pin as wide as possible for improving thermal dissipation.
- ▶ The AGND pin is suggested to connect to 2<sup>nd</sup> GND plate through top to 2<sup>nd</sup> via.
- ▶ For QFN package, please connect RC low pass filter as close as possible to the AVIN pin.
- ▶ Keep current protection setting network as close as possible to the IC. Routing of the network should avoid coupling to high-voltage switching node.
- ▶ Connections from the drivers to the respective gate of the high-side or the low-side MOSFET should be as short as possible to reduce stray inductance.

DS5733-00

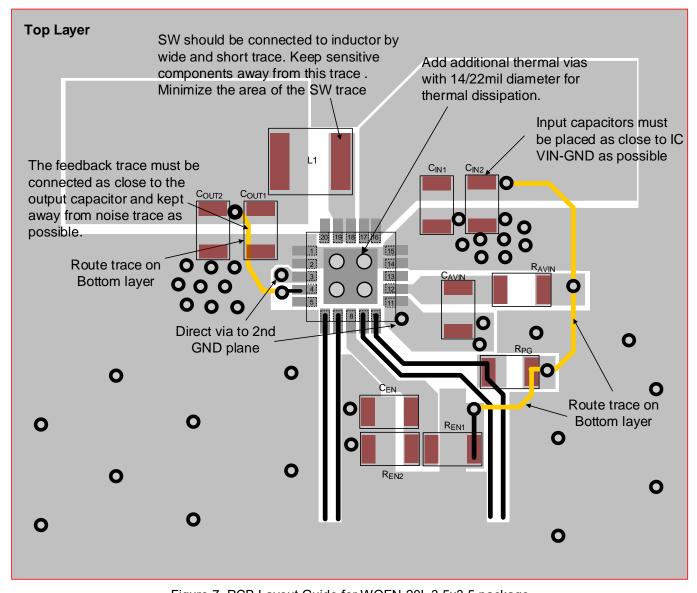


Figure 7. PCB Layout Guide for WQFN-20L 3.5x3.5 package



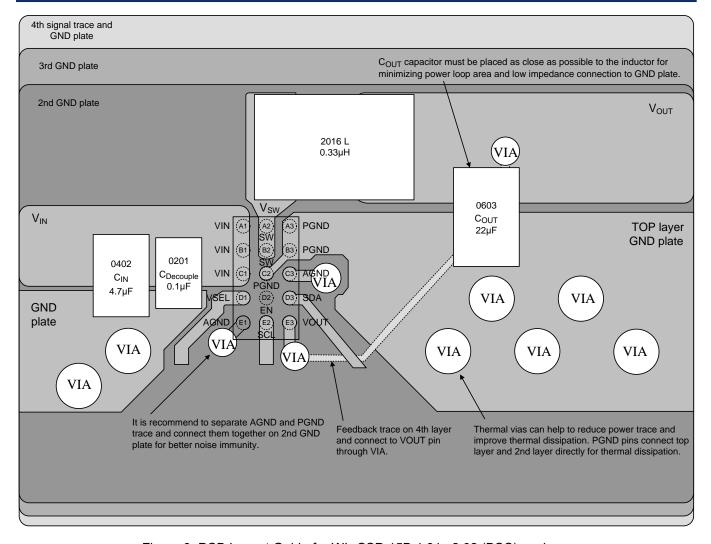
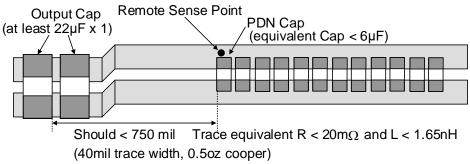


Figure 8. PCB Layout Guide for WL-CSP-15B 1.31x 2.02 (BSC) package



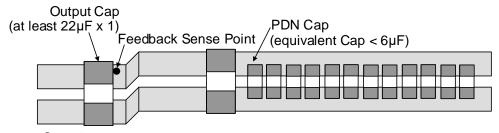
#### **Layout Constraints for Remote Sense Applications**



Case 1:

If the remote sense point is located at PDN cap

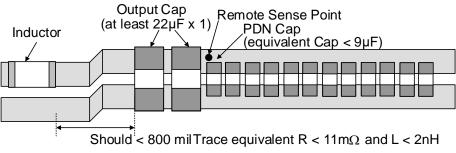
, the distance between  $1^{st}$  22 $\mu F$  cap and PDN cap should not exceed 750 mil.



Case 2:

If the remote sense point is located at 1<sup>st</sup> 22µF cap

, there will be no constraint between  $1^{st}\,22\mu F$  cap and PDN cap yet sacrifice AP transient performance with this configuration.



Case 3: (100mil trace width, 1oz cooper)

If the remote sense point is located at PDN cap and there is long trace between  $1^{st}$  22 $\mu$ F cap and inductor, the distance should not exceed 800mil.

Figure 9. Layout Constraints

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### I<sup>2</sup>C Interface

RT5733AGQW  $I^2C$  slave address is 7'b1010000, and its default output voltage setting is 0.5V/0.9V.  $RT5733AWSC\ I^2C\ slave\ address\ is\ 7'b1010000,\ and\ its\ default\ output\ voltage\ setting\ is\ 0.5V/0.9V.$ 

Address Name	Register Address		Part No.	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
NSEL0 0x0		Meaning	VSEL0								
	0,400	Default	RT5733AGQW	0	0	1	0	0	1	0	1
	UXUU	Delault	RT5733AWSC	0	0	1	0	0	1	0	1
		Read/Write		R/W							
		Meaning				VSE	L1				
NOTIA		Defectly	RT5733AGQW	0	1	1	0	0	1	0	1
NSEL1	0x01	Default	RT5733AWSC	0	1	1	0	0	1	0	1
		Read/Write		R/W							

Address Name		egister ddress	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
		Meaning	DISCHG	UP_S	SR [2:0]	Reserved	SW_RESET		MODE_ VSEL1	MODE_ VSEL0
CONTROL1	0x02	Default	1	0	0	1	0	0	0	0
		Read/Write	R/W	R/W	R/W	R/W	R	R/W	R/W	R/W
		Meaning	VE	NDOR_	ID	Reserved		D	DIE_ID	
ID1	0x03	Default	0	0	0	0	0	0	0	1
		Read/Write	R	R	R	R	R	R	R	R
		Meaning		Re	served			DI	E_REV	
ID2	0x04	Default	0	0	0	0	0	0	0	0
		Read/Write	R	R	R	R	R	R	R	R
		Meaning	PGOOD	UVLO	Reserved	POS	NEG	RESET _ STAT	ОТ	BUCK_ STATUS
MONITOR	0x05	Default	0	0		0	0	0	0	0
		Read/Write	R	R	R	R	R	R	R	R
		Meaning	Di	N_SR[2:	0]	Reserved	SS_S	SR[1:0]	EN_ VSEL1	EN_ VSEL0
CONTROL2	0x06	Default	0	1	1	0	0	0	1	1
		Read/Write	R/W	R/W	R/W	R	R/W	R/W	R/W	R/W
		Meaning	Reser	ved		DIS_DLY[5:0]				
CONTROL4	80x0	Default	0	0	0	0	0	0	0	0
		Read/Write	R	R	R/W	R/W	R/W	R/W	R/W	R/W
CONTROL5	0x0A	Meaning			Rese	ved			LPM	REG_ I2C_ TIME_ OUT
		Default	0	0	0	0	0	0	0	0
		Read/Write	R	R	R	R	R	R	R/W	R/W

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The I<sup>2</sup>C register function description is introduced in the following table.

Register Name	Register Address		Part No.	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)
NSEL0		Meaning	VSEL0								
	0,00	00 Default	RT5733AGQW	0	0	1	0	0	1	0	1
	UXUU		RT5733AWSC	0	0	1	0	0	1	0	1
		Read/Write		R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
	VSEL0			y: 10101: V 00000: 0 r 0.27V to	.27V		′				

Register Name	Regi	ster Address	Part No	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)		
		Meaning	VSEL1										
NSEL1	0x01	Default ⊢	RT5733AGQW	0	1	1	0	0	1	0	1		
NOLLI	OXOT	Delauit	RT5733AWSC	0	1	1	0	0	1	0	1		
		Read/Write		R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W		
	VSEL	1	VID table satisfy SEL[7:0] = 1017  SEL[7:0] = 0000 6.25mV step for	10101: V 00000: 0	.27V		,						



Register Name	Regis	ter Address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)			
		Meaning	DISCHG	U	P_SR[2:	0]	Reserved	SW_ RESET	MODE_ VSEL1	MODE_ VSEL0			
CONTROL1	0x02	Default	1	0 0 1	1	0	0	0	0				
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W			
	DISCHG		0: Disable internal output discharge resistor										
	DISCHG		1: Enable internal output discharge resistor										
UF	UP_SR[2:0]		DVS speed 000 = 25m 001 = 12.5 010 = 6.25 011 = 3.1m 100 = 1.56 101 = 0.75 110 = 0.39 111 = 0.19	V/μs mV/μs mV/μs nV/μs mV/μs mV/μs mV/μs	В ир								
SW	/_RESE	ΕT	Write 1 to reset, always read 0										
MOI	MODE VOELA		0: Auto PFM/PWM mode										
IVIOL	MODE_VSEL1			1: Forced PWM mode									
MOI	MODE VEELO		0: Auto PFM/PWM mode										
IVIOL	MODE_VSEL0		1: Forced PWM mode										

Register Name	Regis	ter Address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)
		Meaning	VENDOR_ID[2:0] Reserve					DIE_	ID[3:0]	
ID1	0x03	Default	0	0	0	0	0	0	0	1
		Read/Write	R	R	R	R	R	R	R	R
VEND	OR_ID	[2:0]	Vendor_ID							
DII	E_ID[3:	0]	DIE_ID							
Register Name	Regis	ter Address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)
		Meaning		Res	erved			DIE_R	EV[3:0]	
ID2	0x04	Default	0	0	0	0	0	0	0	0
		Read/Write	R	R	R	R	R	R	R	R
DIE_REV[3:0]			Revision	_ID						



Register Name	Regis	ter Address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)		
		Meaning	PGOOD	UVLO	Reserved	POS	NEG	RESET_ STAT	ОТ	BUCK_ STATUS		
MONITOR	0x05	Default	0	0	0	0	0	0	0	0		
		Read/Write	R	R	R	R	R	R	R	R		
F	1: Buck is	1: Buck is enabled and soft-start is completed.										
	UVLO		1: Signifies the V <sub>IN</sub> is less than the UVLO threshold.									
	POS		1: Signifies	s a positi	ve voltage tra	ansition i	is in pro	gress				
	NEG		1: Signifies	s a negat	ive voltage tr	ansition	is in pro	ogress				
RES	SET_ST	AT	1: Indicates that a register reset was performed.									
	ОТ		1: Signifies the thermal shutdown is active.									
BUC	BUCK_STATUS			1: Buck enabled; 0: Buck disabled.								

Register Name	Regis	ter Address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)
		Meaning	ι	ON_SR[2:0	]	Reserved	SS_S	R[1:0]	EN_ VSEL1	EN_ VSEL0
CONTROL2	0x06	Default	0	1	1	0	0	0	1	1
	Read/Write R/W R/W R/W R R/W R/W								R/W	R/W
DN	I_SR[2:	0]	DVS spee 000 = 25r 001 = 12. 010 = 6.2 011 = 3.1 100 = 1.5 101 = 0.7 110 = 0.3 111 = 0.1	5mV/μs 5mV/μs mV/μs 6mV/μs 5mV/μs 9mV/μs	down					
SS	5_SR[1:	0]	DVS spee 00 = 10m 01 = 5mV 10 = 2.5m 11 = 1.25	//μs ۱V/μs	start DVS					
EN	I_VSEL	.1	Software power-on/off control register (activate when the VSEL pin se high): 0: Disable output 1: Enable output							to logic-
Software power-on/off control register (activate when the VSEL pin low): 0: Disable output 1: Enable output						EL pin set	to logic-			

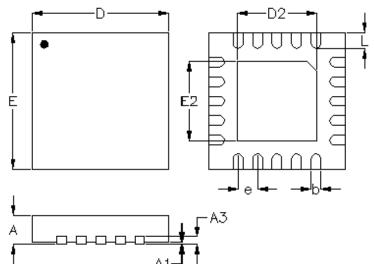


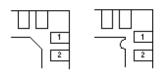
Register Name	Redister Address		b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)		
	Meaning			erved	DIS_DLY[5:0]							
CONTROL4	0x08	Default	0	0	0	0	0	0	0	0		
		Read/Write	R	R	R/W	R/W	R/W	R/W	R/W	R/W		
DIS_DLY[5:0]					n disable (i 11111b =	,	eps of 1ms	s)				

Register Name	Regis	ter Address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)			
		Meaning			Rese	erved			LPM	REG_I2C_ TIME_OUT			
CONTROL5	CONTROL5 0x0A Default		0	0	0	0	0	0	0	0			
		Read/Write	R	R	R/W	R/W	R/W	R/W	R/W	R/W			
	LPM				Low power mode (LPM) control register: 0: Disable low power mode function 1: Enable low power mode function for power saving.								
REG_l2	E_OUT	I <sup>2</sup> C time-out control register:  0: Disable I <sup>2</sup> C time-out feature  1: Enable I <sup>2</sup> C time-out feature to prevent from system hangout situation; the device will automatically reset I <sup>2</sup> C to restore communication.											



### **Outline Dimension**





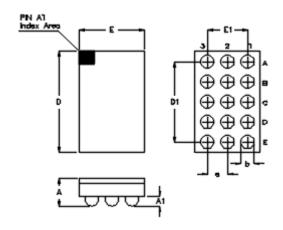
Pin #1 ID and Tie Bar Mark Options

Note: The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Comple ed	Dimensions	n Millimeters	Dimension	s In Inches
Symbol	Min	Max	Min	Max
А	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
А3	0.175	0.250	0.007	0.010
b	0.200	0.300	0.008	0.012
D	3.400	3.600	0.134	0.142
D2	2.000	2.100	0.079	0.083
E	3.400	3.600	0.134	0.142
E2	2.000	2.100	0.079	0.083
е	0.5	500	0.0	)20
L	0.350	0.450	0.014	0.018

W-Type 20L QFN 3.5x3.5 Package



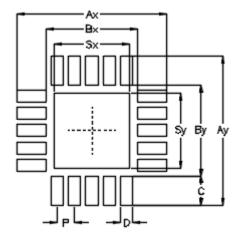


Sumb al	Dimensions I	n Millimeters	Dimensions In Inches				
Symbol	Min	Max	Min	Max			
Α	0.500	0.600	0.020	0.024			
A1	0.170	0.230	0.007	0.009			
b	0.240	0.300	0.009	0.012			
D	1.980	2.060	0.078	0.081			
D1	1.6	600	0.063				
E	1.270	1.350	0.050	0.053			
E1	0.8	800	0.031				
е	0.4	100	0.016				

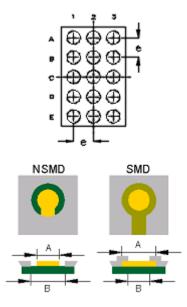
15B WL-CSP 1.31x2.02 Package (BSC)



# **Footprint Information**



Dookogo	Number of		Footprint Dimension (mm)								
Package	Pin	Р	Ax	Ау	Вх	Ву	С	D	Sx	Sy	Tolerance
V/W/U/XQFN3.5*3.5-20	20	0.50	4.30	4.30	2.60	2.60	0.85	0.35	2.15	2.15	±0.05

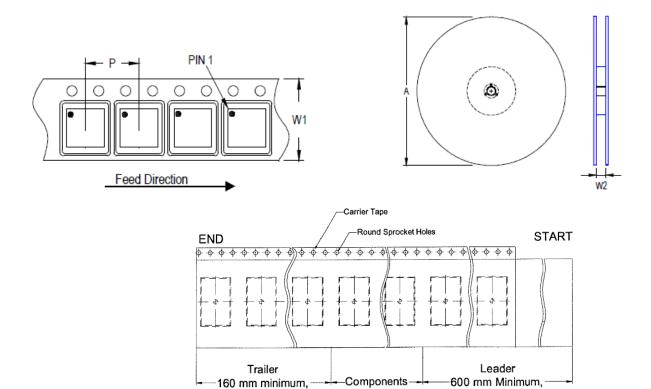


Dookogo	Number of		Footpri	nt Dimensio	n (mm)	Toloropoo
Package	Pin	Type	е	Α	В	Tolerance
\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	15	NSMD	0.400	0.240	0.340	.0.02F
WL-CSP1.31*2.02-15(BSC)	15	SMD	0.400	0.270	0.240	±0.025

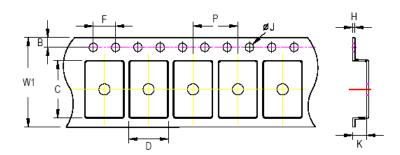


## **Packing Information**

### Tape and Reel Data (QFN/DFN 3.5x3.5)



Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)			Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min./Max. (mm)
QFN/DFN 3.5x3.5	12	8	180	7	1,500	160	600	12.4/14.4



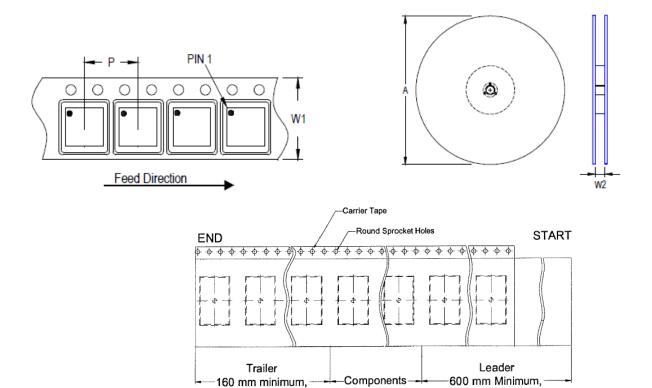
C, D and K are determined by component size. The clearance between the components and the cavity is as follows:

- For 12mm carrier tape: 0.5mm max.

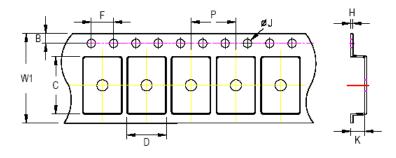
Tape Size	W1	F	)	E	3	F	-	Ø	IJ	Н
Tape Size	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.
12mm	12.3mm	7.9mm	8.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	0.6mm



### Tape and Reel Data (WL-CSP 1.31x2.02)



Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)	Reel Size (A) (mm) (in)		Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min./Max. (mm)
WL-CSP 1.31x2.02	8	4	180	7	3,000	160	600	8.4/9.9



C, D and K are determined by component size. The clearance between the components and the cavity is as follows:

- For 8mm carrier tape: 0.5mm max.

Tape Size	W1	F	)	E	3	ı		Ø	IJ	Н
Tape Size	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.
8mm	8.3mm	3.9mm	4.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	0.6mm

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### Tape and Reel Packing (QFN/DFN 3.5x3.5)

Step	Photo/Description	Step	Photo/Description
1	Reel 7"	4	RICHTER (1962)  RICHTER (1962)
2	HIC & Desiccant (1 Unit) inside	5	12 inner boxes per outer box
3	Caution label is on backside of Al bag	6	Outer box Carton A

Container	R	eel			Вох	Зох			Carton			
Package	Size	Units	Item	Size(cm)	Weight(Kg)	Reels	Units	Item	Size(cm)	Boxes	Unit	
QFN/DFN	7"		Box A	18.3*18.3*8.0	0.1	3	4,500	Carton A	38.3*27.2*38.3	12	54,000	
3.5x3.5	7"	1,500	Box E	18.6*18.6*3.5	0.03	1	1,500		For Combined or Ur	n-full Reel.		



### Tape and Reel Packing (WL-CSP 1.31x2.02)

Step	Photo/Description	Step	Photo/Description
1	RICHTEK 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	4	
	Reel 7"		12 inner boxes per outer box
2	BUSTISSES OF THE PROPERTY OF T	5	RICHTEK RICE SERVICE STATE OF THE PARTY OF T
	Packing by Anti-Static Bag		Outer box Carton A
3	RICHTEK States  RICHTEK STATES	6	
	3 reels per inner box <b>Box A</b>		

Container	R	eel		Вох				Carton		
Package	Size	Units	Item	Size(cm)	Reels	Units	Item	Size(cm)	Boxes	Unit
WL-CSP	7"	2 000	Box A	18.3*18.3*8.0	3	9,000	Carton A	38.3*27.2*38.3	12	108,000
1.31x2.02	1	3,000	Box E	18.6*18.6*3.5	1	3,000		For Combined or Ur	n-full Reel.	



### **Packing Material Anti-ESD Property**

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
$\Omega$ /cm $^2$	10 <sup>4</sup> ~ 10 <sup>11</sup>					

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### **Datasheet Revision History**

Version	Date	Description	Item
00	2023/2/1	Final	